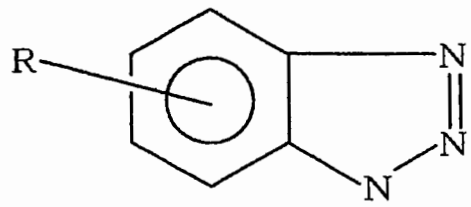
POLISHING COMPOSITION AND POLISHING METHOD

ABSTRACT

To provide a polishing composition which has a high removal rate and enables to suppress occurrence of dishing and erosion, in polishing of a surface to be polished in the production of a semiconductor integrated circuit device. A chemical mechanical polishing composition for polishing a surface to be polished of semiconductor integrated circuit devices comprises (A) fine oxide particles, (B) pullulan, and (C) water. The polishing composition further contains (D) an oxidizing agent, and (E) a compound represented by the formula 1:



Formula 1

wherein R is a hydrogen atom, a C_{1-4} alkyl group, a C_{1-4} alkoxy group or a carboxylic acid group.

Figure 1